BLM9D2527-20AB

LDMOS 2-stage integrated Doherty MMIC

AMPLEON

Rev. 1 — 29 June 2017

Product data sheet

1. Product profile

1.1 General description

The BLM9D2527-20AB is a 2-stage fully integrated Doherty MMIC solution using Ampleon's state of the art GEN9 LDMOS technology. The carrier and peaking device, input splitter and output combiner are integrated in a single package. This multiband device is perfectly suited as a final device in massive MIMO or small cell applications in the frequency range from 2500 MHz to 2700 MHz. Available in PQFN outline.

Table 1. Performance

Typical RF performance at T_{case} = 25 °C; I_{Dq} = 43 mA (driver and final stages); $V_{GSq(peaking)} = V_{GSq(carrier)} - 0.75$ V. Test signal: 3GPP test model 1; 64 DPCH; PAR = 9.9 dB at 0.01 % probability on CCDF.

Test signal	f	V _{DS}	P _{L(AV)}	Gp	ηр	ACPR _{5M}
	(MHz)	(V)	(W)	(dB)	(%)	(dBc)
single carrier W-CDMA	2620	28	3.8	27.3	46.1	-33.3

1.2 Features and benefits

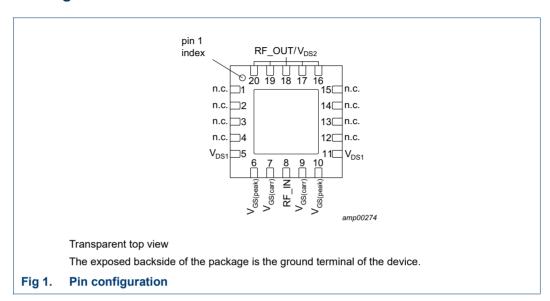
- Integrated input splitter
- Integrated output combiner
- Very high efficiency thanks to asymmetry
- Designed for broadband operation (frequency 2500 MHz to 2700 MHz)
- Independent control of carrier and peaking bias
- Integrated ESD protection
- Excellent thermal stability
- Source impedance 50 Ω ; high power gain
- Compliant to Directive 2002/95/EC, regarding restriction of hazardous substances (RoHS)

1.3 Applications

■ RF power MMIC for multi-carrier and multi-standard GSM, W-CDMA and LTE base stations in the 2500 MHz to 2700 MHz frequency range.

2. Pinning information

2.1 Pinning



2.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
n.c.	1	not connected
n.c.	2	not connected
n.c.	3	not connected
n.c.	4	not connected
V _{DS1}	5	drain-source voltage of driver stages
V _{GS(peak)}	6	gate-source voltage of peaking
V _{GS(carr)}	7	gate-source voltage of carrier
RF_IN	8	RF input
V _{GS(carr)}	9	gate-source voltage of carrier
V _{GS(peak)}	10	gate-source voltage of peaking
V _{DS1}	11	drain-source voltage of driver stages
n.c.	12	not connected
n.c.	13	not connected
n.c.	14	not connected
n.c.	15	not connected
RF_OUT/V _{DS2}	16	RF output / drain-source voltage of final stages
RF_OUT/V _{DS2}	17	RF output / drain-source voltage of final stages
RF_OUT/V _{DS2}	18	RF output / drain-source voltage of final stages

Table 2. Pin description ...continued

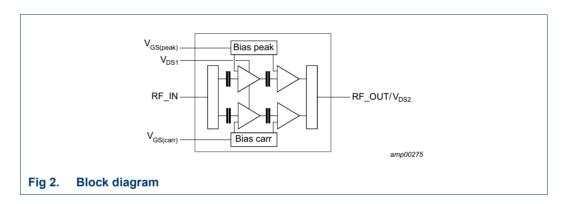
Symbol	Pin	Description
RF_OUT/V _{DS2}	19	RF output / drain-source voltage of final stages
RF_OUT/V _{DS2}	20	RF output / drain-source voltage of final stages
GND	flange	RF ground

3. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
BLM9D2527-20AB		plastic thermal enhanced quad flat package; no leads; 20 terminals; body 8.0 x 8.0 x 2.1 mm	SOT1462-1			

4. Block diagram



5. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage		-	65	V
V_{GS}	gate-source voltage		-0.5	+13	V
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature	<u>[1]</u>	-	175	°C

^[1] Continuous use at maximum temperature will affect the reliability. For details refer to the online MTF calculator.

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Thermal characteristics 6.

Table 5. Thermal characteristics

Measured for total device.

Symbol	Parameter	Conditions	Value	Unit
R _{th(j-c)}	thermal resistance from junction to	$T_{case} = 90 ^{\circ}C; P_{L(AV)} = 3 W$ [1]	12	K/W
	case	T _{case} = 90 °C; P _{L(AV)} = 1.25 W [1]	17	K/W

^[1] When operated with a 1-carrier W-CDMA with PAR = 8 dB.

Characteristics 7.

Table 6. DC characteristics

 $T_{case} = 25$ °C; unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit	
Carrier			'				
V_{GSq}	gate-source quiescent voltage	V_{DS} = 28 V; I_{D} = 37 mA	1.65	2.2	2.75	V	
I _{GSS}	gate leakage current	V _{GS} = 1 V; V _{DS} = 0 V	-	-	140	nA	
Peaking							
I _{GSS}	gate leakage current	V _{GS} = 1 V; V _{DS} = 0 V	-	-	140	nA	
Final sta	ges						
I _{DSS}	drain leakage current	V _{GS} = 0 V; V _{DS} = 28 V	-	-	1.4	μА	
Driver st	Driver stages						
I _{DSS}	drain leakage current	V _{GS} = 0 V; V _{DS} = 28 V	-	-	1.4	μА	

RF Characteristics

Typical RF performance at T_{case} = 25 °C; V_{DS} = 28 V; I_{Dq} = 37 mA (carrier); $V_{GSq(peaking)} = V_{GSq(carrier)} - 0.5$ V; P_L = 2 W; f = 2.7 GHz. Unless otherwise specified, measured in an Ampleon production circuit.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Test sign	al: CW		'			
Gp	power gain		26	27.2	29	dB
η_{D}	drain efficiency	P _L = 2 W	36	41	-	%
		$P_L = P_{L(3dB)}$	50	56	-	%
RLin	input return loss		-	-19	-10	dB
P _{L(3dB)}	output power at 3 dB gain compression		43	43.6	-	dBm

8. Application information

Table 8. Typical performance

Test signal: 1-carrier W-CDMA; $T_{case} = 25 \, ^{\circ}\text{C}$; $V_{DS} = 28 \, ^{\circ}\text{V}$; $I_{Dq} = 43 \, \text{mA}$ (driver and final stages); test model 1; 64 DPCH; $PAR = 9.9 \, \text{dB}$ at 0.01 % probability CCDF; unless otherwise specified, measured in an Ampleon 2620 MHz to 2690 MHz frequency band asymmetrical Doherty application circuit.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
P _{L(3dB)}	output power at 3 dB gain compression	f = 2655 MHz	[1]	-	43.4	-	dBm
φ _{s21} /φ _{s21(norm)}	normalized phase response	f = 2655 MHz; at 3 dB compression point	[2]	-	-14.5	-	0
η_{D}	drain efficiency	8 dB OBO (P _{L(AV)} = 35.8 dBm); f = 2620 MHz		-	46.1	-	%
Gp	power gain	P _{L(AV)} = 35.8 dBm; f = 2620 MHz		-	27.3	-	dB
B _{video}	video bandwidth	P _{L(AV)} = 34.5 dBm set to obtain IMD3 = -30 dBc; 2-tone CW; f = 2655 MHz		-	265	-	MHz
G _{flat}	gain flatness	P _{L(AV)} = 35.8 dBm; f = 2620 MHz to 2170 MHz		-	0.2	-	dB
ACPR _{5M}	adjacent channel power ratio (5M)	P _{L(AV)} = 35.8 dBm; f = 2655 MHz		-	-33.3	-	dBc
ΔG/ΔT	gain variation with temperature	f = 2655 MHz		-	0.04	-	dB/°C
К	Rollett stability factor	T_{case} = -40 °C; f = 0.15 GHz to 5 GHz	[3]	-	>1.7	-	

^[1] Pulsed CW power sweep measurement (δ = 10 %, t_p = 100 μ s).

^{[2] 25} ms CW power sweep measurement.

^[3] S-parameters measured with load-pull jig.

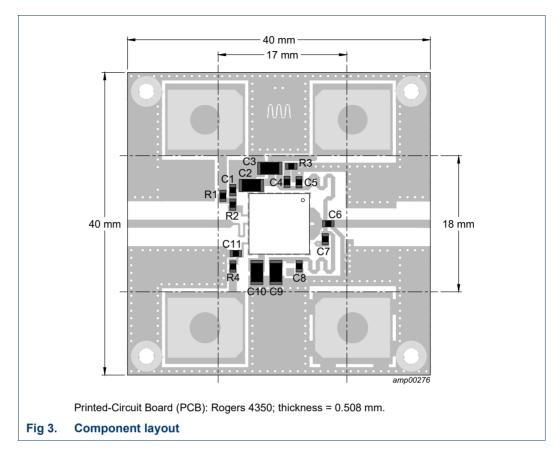
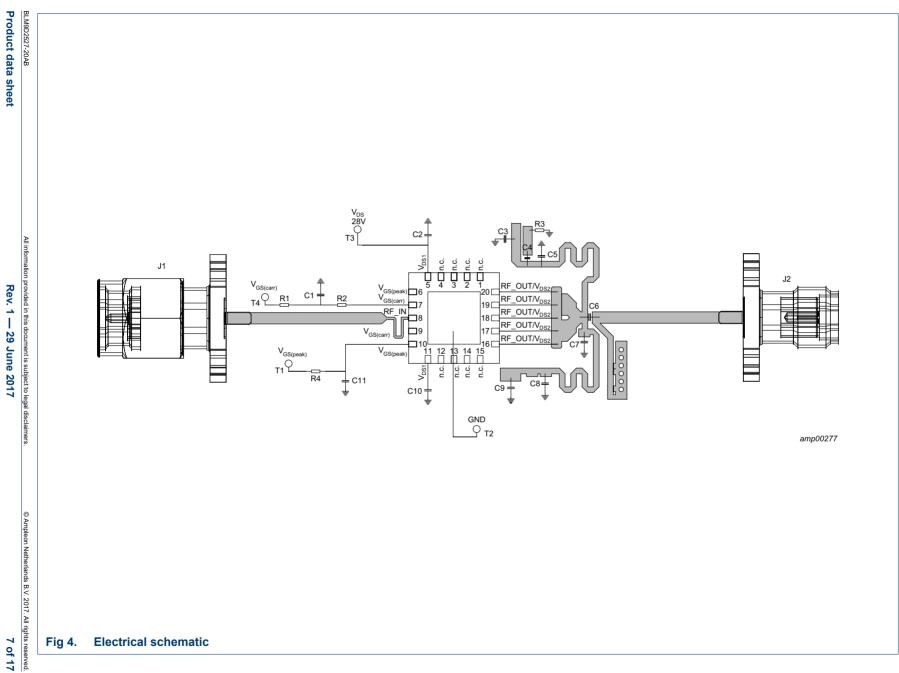


Table 9.Demo test circuit list of componentsSee Figure 3 for component layout.

Component	Description	Value	Remarks
C1, C11	multilayer ceramic chip capacitor	10 μF, 50 V	Murata: GRM31CR61H106KA12L
C2, C3, C9, C10	multilayer ceramic chip capacitor	1 μF, 6.3 V	TDK: C1608X5R0J106K080AB
C4	multilayer ceramic chip capacitor	100 pF	Murata: GQM1875C2E1R6BB12
C5, C8	multilayer ceramic chip capacitor	4.7 pF	Murata: GQM1875C2E5R6BB12
C6	multilayer ceramic chip capacitor	1.8 pF	Murata: GQM1875C2E7R5BB12
C7	multilayer ceramic chip capacitor	1.6 pF	Murata: GQM1875C2ER50BB12
J1	SMA Coaxial panel connector male		Hubner & Suhner: 13_SMA-50-0-2/111_N
J2	SMA Coaxial panel connector female		Hubner & Suhner: 13_SMA-50-0-2/111_N
R1	SMD resistor	820 Ω, ±1 %	Multicomp: MC805
R2	SMD resistor	5.1 Ω, ±1 %	Multicomp: MC805
R3, R4	SMD resistor	10 Ω, ±1 %	Multicomp: MC805
T1, T2, T3, T4	PCB Terminal	6.35 mm × 0.81 mm; 4.1 mm	TE connectivity



8.1 Ruggedness in a Doherty operation

The BLM9D2527-20AB is capable of withstanding a load mismatch corresponding to VSWR = 10 : 1 through all phases under the following conditions: V_{DS} = 32 V; I_{Dq} = 37 mA (carrier); $V_{GSq(peaking)} = V_{GSq(carrier)} - 0.5$ V; P_i corresponding to $P_{L(3dB)}$ under Z_S = 50 Ω load; f = 2700 MHz (CW); T_{case} = 25 °C.

8.2 Impedance information

Table 10. Typical impedance for optimum Doherty operation

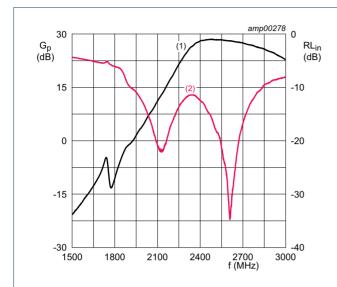
Measured load-pull data per section; test signal: pulsed CW; $T_{case} = 25$ °C; $V_{DS} = 28$ V; $I_{Dq} = 35$ mA (carrier); $V_{GSq(peaking)} = V_{GSq(carrier)} - 0.5$ V; $t_p = 100$ μ s; $\delta = 10$ %. Typical values.

	tuned for optimum Do	tuned for optimum Doherty operation					
f	Z _L	G _{p(max)}	P_L	η _{add} [1]	η _{add} [2]		
(MHz)	(Ω)	(dB)	(dBm)	(%)	(%)		
2450	4.97 – j0.76	28.60	43.80	51.00	51.30		
2500	5.48 - j0.92	28.60	43.80	51.20	52.80		
2500	5.97 – j1.02	28.40	43.90	53.30	52.20		
2600	6.73 – j1.22	28.30	43.70	53.80	52.00		
2650	7.20 – j1.31	28.20	43.70	54.70	52.10		
2700	7.59 – j1.21	28.20	43.60	56.50	52.40		
2750	7.93 – j1.04	28.00	43.50	56.60	50.30		

^[1] at 43 dBm (nearly 3 dB compression point).

^[2] at 35 dBm (nearly 8 dB OBO point).

8.3 Graphs



 T_{case} = 25 °C; V_{DS} = 28 V; P_{L} = 1 W;

 $I_{Dq1} + I_{Dq2} = 43 \text{ mA (carrier and peaking stages)};$

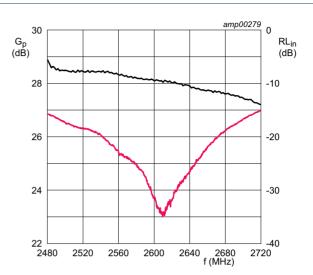
V_{GS} = 2.29 V (carrier stage);

V_{GS} = 1.54 V (peaking stage).

Test signal: CW.

- (1) magnitude of G_D
- (2) magnitude of RLin

Fig 5. Wideband power gain and input return loss as function of frequency; typical values



 T_{case} = 25 °C; V_{DS} = 28 V; P_{L} = 1 W;

 $I_{Dq1} + I_{Dq2} = 43 \text{ mA}$ (carrier and peaking stages);

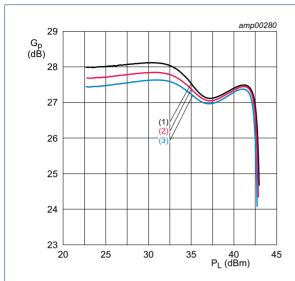
V_{GS} = 2.29 V (carrier stage);

V_{GS} = 1.54 V (peaking stage).

Test signal: CW.

- (1) magnitude of G_p
- (2) magnitude of RLin

Fig 6. In-band power gain and input return loss as function of frequency; typical values



 T_{case} = 25 °C; V_{DS} = 28 V;

 $I_{Dq1} + I_{Dq2} = 43 \text{ mA}$ (carrier and peaking stages);

V_{GS} = 2.29 V (carrier stage);

V_{GS} = 1.54 V (peaking stage).

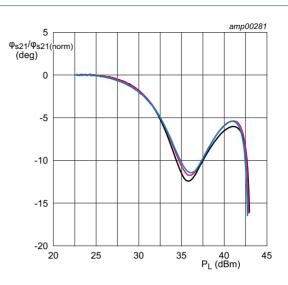
Test signal: CW.

(1) f = 2620 MHz

(2) f = 2655 MHz

(3) f = 2690 MHz

Fig 7. Power gain as a function of output power; typical values



 T_{case} = 25 °C; V_{DS} = 28 V;

 $I_{Dq1} + I_{Dq2} = 43 \text{ mA}$ (carrier and peaking stages);

 $V_{GS} = 2.29 \text{ V (carrier stage)};$

V_{GS} = 1.54 V (peaking stage).

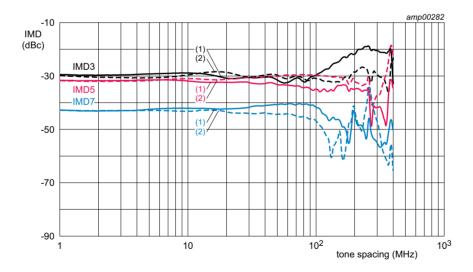
Test signal: CW.

(1) f = 2620 MHz

(2) f = 2655 MHz

(3) f = 2690 MHz

Fig 8. Normalized phase response as a function of output power; typical values



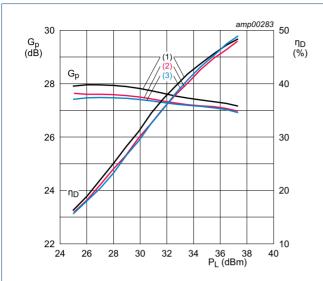
 T_{case} = 25 °C; V_{DS} = 28 V; P_L = 34.5 dBm; I_{Dq1} + I_{Dq2} = 43 mA (carrier and peaking stages); V_{GS} = 2.29 V (carrier stage); V_{GS} = 1.54 V (peaking stage).

Test signal: CW.

(1) IMD low

(2) IMD high

Fig 9. Intermodulation distortion as a function of tone spacing; typical values



 T_{case} = 25 °C; V_{DS} = 28 V;

 $I_{Dq1} + I_{Dq2} = 43 \text{ mA}$ (carrier and peaking stages);

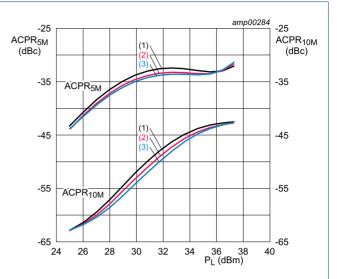
 $V_{GS} = 2.29 \text{ V (carrier stage)};$

V_{GS} = 1.54 V (peaking stage).

Test signal: 1-carrier W-CDMA; test model 1; 64 DPCH; PAR = 9.9 dB at 0.01 % probability CCDF.

- (1) f = 2620 MHz
- (2) f = 2655 MHz
- (3) f = 2690 MHz

Fig 10. Power gain and drain efficiency as function of output power; typical values



 T_{case} = 25 °C; V_{DS} = 28 V;

 $I_{Dq1} + I_{Dq2} = 43 \text{ mA}$ (carrier and peaking stages);

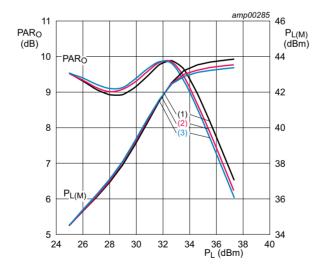
V_{GS} = 2.29 V (carrier stage);

V_{GS} = 1.54 V (peaking stage).

Test signal: 1-carrier W-CDMA; test model 1; 64 DPCH; PAR = 9.9 dB at 0.01 % probability CCDF.

- (1) f = 2620 MHz
- (2) f = 2655 MHz
- (3) f = 2690 MHz

Fig 11. Adjacent channel power ratio as a function of output power; typical values



 T_{case} = 25 °C; V_{DS} = 28 V; I_{Dq1} + I_{Dq2} = 43 mA (carrier and peaking stages);

 V_{GS} = 2.29 V (carrier stage); V_{GS} = 1.54 V (peaking stage).

Test signal: 1-carrier W-CDMA; test model 1; 64 DPCH; PAR = 9.9 dB at 0.01 % probability CCDF.

- (1) f = 2620 MHz
- (2) f = 2655 MHz
- (3) f = 2690 MHz

Fig 12. Output peak-to-average ratio and peak output power as function of output power; typical values

9. Package outline

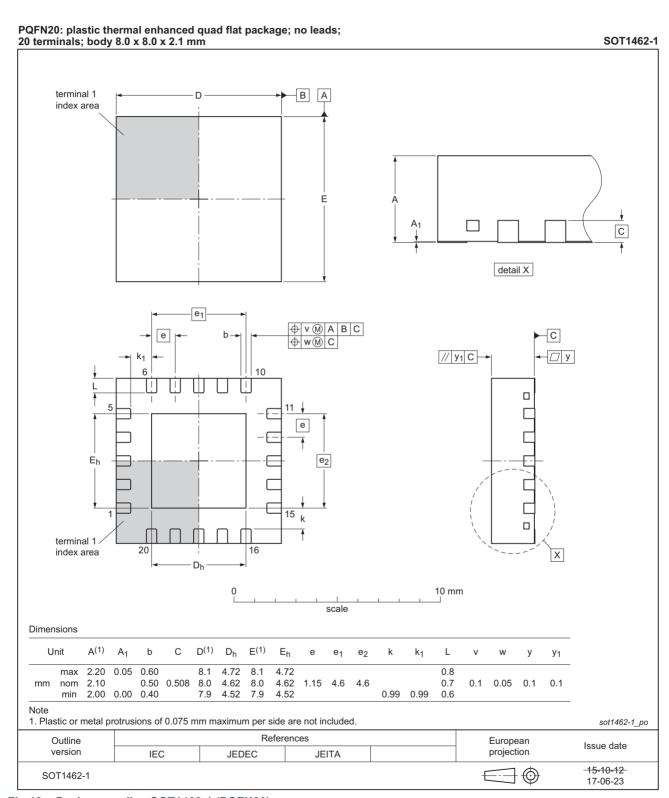


Fig 13. Package outline SOT1462-1 (PQFN20)

10. Handling information

CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the ANSI/ESD S20.20, IEC/ST 61340-5, JESD625-A or equivalent standards.

Table 11. ESD sensitivity

ESD model	Class
Charged Device Model (CDM); According to ANSI/ESDA/JEDEC standard JS-002	C2B [1]
Human Body Model (HBM); According to ANSI/ESDA/JEDEC standard JS-001	1B 🛂

^[1] CDM classification C2B is granted to any part that passes after exposure to an ESD pulse of 750 V, but fails after exposure to an ESD pulse of 1000 V.

11. Abbreviations

Table 12. Abbreviations

Acronym	Description
AM	Amplitude Modulation
3GPP	3rd Generation Partnership Project
CCDF	Complementary Cumulative Distribution Function
CW	Continuous Wave
DPCH	Dedicated Physical CHannel
ESD	ElectroStatic Discharge
GEN9	Ninth Generation
GSM	Global System for Mobile Communications
LDMOS	Laterally Diffused Metal Oxide Semiconductor
LTE	Long Term Evolution
MIMO	Multiple Input Multiple Output
MMIC	Monolithic Microwave Integrated Circuit
MTF	Median Time to Failure
ОВО	Output Back Off
PAR	Peak-to-Average Ratio
PM	Phase Modulation
SMD	Surface Mounted Device
VSWR	Voltage Standing-Wave Ratio
W-CDMA	Wideband Code Division Multiple Access

^[2] HBM classification 1B is granted to any part that passes after exposure to an ESD pulse of 500 V, but fails after exposure to an ESD pulse of 1000 V.

12. Revision history

Table 13. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BLM9D2527-20AB v.1	20170629	Product data sheet	-	-

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13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions"
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BLM9D2527-20AB

LDMOS 2-stage integrated Doherty MMIC

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